

2.5 Ω Quad SPST Switches in Chip Scale Package

ADG781/ADG782/ADG783

FEATURES

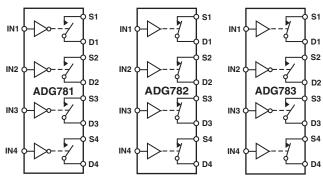
1.8 V to 5.5 V Single Supply Low On Resistance (2.5 Ω Typ) Low On-Resistance Flatness (0.5 Ω) –3 dB Bandwidth > 200 MHz Rail-to-Rail Operation 20-Lead 4 mm \times 4 mm Chip Scale Package Fast Switching Times $t_{ON} = 16$ ns $t_{OFF} = 10$ ns

t_{OFF} = 10 ns
Typical Power Consumption (< 0.01 μW)
TTL/CMOS Compatible
For Functionally Equipolant Devices in 16

For Functionally Equivalent Devices in 16-Lead TSSOP and SOIC Packages, See ADG711/ADG712/ADG713

APPLICATIONS
Battery Powered Systems
Communication Systems
Sample Hold Systems
Audio Signal Routing
Video Switching
Mechanical Reed Relay Replacement

FUNCTIONAL BLOCK DIAGRAMS



SWITCHES SHOWN FOR A LOGIC "1" INPUT

GENERAL DESCRIPTION

The ADG781, ADG782, and ADG783 are monolithic CMOS devices containing four independently selectable switches. These switches are designed on an advanced submicron process that provides low power dissipation and high switching speed, low on resistance, low leakage currents and high bandwidth.

They are designed to operate from a single 1.8 V to 5.5 V supply, making them ideal for use in battery powered instruments and with the new generation of DACs and ADCs from Analog Devices. Fast switching times and high bandwidth make the part suitable for video signal switching.

The ADG781, ADG782, and ADG783 contain four independent single-pole/single throw (SPST) switches. The ADG781 and ADG782 differ only in that the digital control logic is inverted. The ADG781 switches are turned on with a logic low on the appropriate control input, while a logic high is required to turn on the switches of the ADG782. The ADG783 contains two switches whose digital control logic is similar to the ADG781, while the logic is inverted on the other two switches.

Each switch conducts equally well in both directions when ON. The ADG783 exhibits break-before-make switching action.

The ADG781/ADG782/ADG783 are available in 20-lead chip scale packages.

PRODUCT HIGHLIGHTS

- 1. 20-Lead 4 mm \times 4 mm Chip Scale Package (CSP).
- 1.8 V to 5.5 V Single Supply Operation. The ADG781, ADG782, and ADG783 offer high performance and are fully specified and guaranteed with 3 V and 5 V supply rails.
- 3. Very Low R_{ON} (4.5 Ω max at 5 V, 8 Ω max at 3 V). At supply voltage of 1.8 V, R_{ON} is typically 35 Ω over the temperature range.
- 4. Low On-Resistance Flatness.
- 5. -3 dB Bandwidth >200 MHz.
- 6. Low Power Dissipation. CMOS construction ensures low power dissipation.
- 7. Fast t_{ON}/t_{OFF}.
- 8. Break-Before-Make Switching. This prevents channel shorting when the switches are configured as a multiplexer (ADG783 only).

REV.C

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$\begin{array}{ll} \textbf{ADG781/ADG782/ADG783-SPECIFICATIONS} & (V_{DD}=5 \text{ V} \pm 10\%, \text{ GND}=0 \text{ V}. \text{ All specifications} \\ -40^{\circ}\text{C to} +85^{\circ}\text{C unless otherwise noted.}) \end{array}$

	B Version				
Parameter	+25°C	-40°C to +85°C	Unit	Test Conditions/Comments	
ANALOG SWITCH					
Analog Signal Range		$0~\mathrm{V}$ to V_{DD}	V		
On Resistance (R _{ON})	2.5	· · · · · · · · · · · · · · · · · · ·	Ω typ	$V_S = 0 \text{ V to } V_{DD}, I_S = -10 \text{ mA};$	
olv	4	4.5	Ω max	Test Circuit 1	
On-Resistance Match Between		0.05	Ω typ	$V_S = 0 \text{ V to } V_{DD}, I_S = -10 \text{ mA}$	
Channels (ΔR_{ON})		0.4	Ω max	<i>BB</i> 5	
On-Resistance Flatness (R _{FLAT(ON)})	0.5		Ω typ	$V_S = 0 \text{ V to } V_{DD}, I_S = -10 \text{ mA}$	
(1221)		1.0	Ω max		
LEAKAGE CURRENTS				V _{DD} = 5.5 V;	
Source OFF Leakage I _S (OFF)	±0.01		nA typ	$V_S = 4.5 \text{ V/1 V}, V_D = 1 \text{ V/4.5 V};$	
	±0.1	± 0.2	nA max	Test Circuit 2	
Drain OFF Leakage I _D (OFF)	±0.01		nA typ	$V_S = 4.5 \text{ V/1 V}, V_D = 1 \text{ V/4.5 V};$	
	±0.1	± 0.2	nA max	Test Circuit 2	
Channel ON Leakage ID, IS (ON)	±0.01		nA typ	$V_S = V_D = 1 \text{ V, or } 4.5 \text{ V;}$	
0 5. 5 . ,	±0.1	± 0.2	nA max	Test Circuit 3	
DIGITAL INPUTS					
Input High Voltage, V _{INH}		2.4	V min		
Input Low Voltage, V _{INL}		0.8	V max		
Input Current					
I _{INL} or I _{INH}	0.005		μA typ	$V_{IN} = V_{INL}$ or V_{INH}	
		± 0.1	μA max		
DYNAMIC CHARACTERISTICS ²					
t_{ON}	11		ns typ	$R_L = 300 \Omega, C_L = 35 pF,$	
		16	ns max	$V_S = 3 V$; Test Circuit 4	
t_{OFF}	6		ns typ	$R_L = 300 \Omega, C_L = 35 pF,$	
		10	ns max	$V_S = 3 V$; Test Circuit 4	
Break-Before-Make Time Delay, t _D	6		ns typ	$R_L = 300 \Omega, C_L = 35 pF,$	
(ADG783 Only)		1	ns min	$V_{S1} = V_{S2} = 3 \text{ V}$; Test Circuit 5	
Charge Injection	3		pC typ	$V_S = 2 V$; $R_S = 0 \Omega$, $C_L = 1 nF$; Test Circuit 6	
Off Isolation	-58		dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 10 MHz$	
	-78		dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; Test Circuit 7	
Channel-to-Channel Crosstalk	-90		dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 10 MHz$; Test Circuit 8	
Bandwidth -3 dB	200		MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; Test Circuit 9	
$C_{S}(OFF)$	10		pF typ	f = 1 MHz	
C_D (OFF)	10		pF typ	f = 1 MHz	
$C_D, C_S(ON)$	22		pF typ	f = 1 MHz	
POWER REQUIREMENTS				$V_{\mathrm{DD}} = 5.5 \mathrm{V}$	
I_{DD}	0.001		μA typ	Digital Inputs = 0 V or 5.5 V	
		1.0	μA max		

NOTES

¹Temperature ranges are as follows: B Version: −40°C to +85°C.

²Guaranteed by design, not subject to production test.

Specifications subject to change without notice.

 $\label{eq:continuous} \textbf{SPECIFICATIONS}^{1} \quad \text{(V}_{DD} = 3 \text{ V} \pm 10\%, \text{ GND} = 0 \text{ V}. \text{ All specifications} -40^{\circ}\text{C to} +85^{\circ}\text{C unless otherwise noted.)}$

	B Version				
Parameter	+25°C	-40°C to +85°C	Unit	Test Conditions/Comments	
	+23 C	+63 C	Cint	Test Conditions/Comments	
ANALOG SWITCH		0.11	**		
Analog Signal Range	_	0 V to V_{DD}	V		
On Resistance (R _{ON})	5	5.5	Ω typ	$V_S = 0 \text{ V to } V_{DD}, I_S = -10 \text{ mA};$	
0. D. 1. 1. D.		10	Ω max	Test Circuit 1	
On-Resistance Match Between	0.1	0.5	Ω typ	$V_S = 0 \text{ V to } V_{DD}, I_S = -10 \text{ mA}$	
Channels (ΔR_{ON})		0.5	Ω max		
On-Resistance Flatness (R _{FLAT(ON)})		2.5	Ω typ	$V_S = 0 \text{ V to } V_{DD}, I_S = -10 \text{ mA}$	
LEAKAGE CURRENTS				$V_{\rm DD} = 3.3 \text{ V};$	
Source OFF Leakage I _S (OFF)	±0.01		nA typ	$V_S = 3 \text{ V/1 V}, V_D = 1 \text{ V/3 V};$	
	±0.1	± 0.2	nA max	Test Circuit 2	
Drain OFF Leakage I _D (OFF)	±0.01		nA typ	$V_S = 3 \text{ V/1 V}, V_D = 1 \text{ V/3 V};$	
	±0.1	± 0.2	nA max	Test Circuit 2	
Channel ON Leakage ID, IS (ON)	±0.01		nA typ	$V_S = V_D = 1 \text{ V, or } 3 \text{ V;}$	
	±0.1	± 0.2	nA max	Test Circuit 3	
DIGITAL INPUTS					
Input High Voltage, V _{INH}		2.0	V min		
Input Low Voltage, V _{INL}		0.8	V max		
Input Current					
I _{INL} or I _{INH}	0.005		μA typ	$V_{IN} = V_{INI}$ or V_{INH}	
		± 0.1	μA max		
DYNAMIC CHARACTERISTICS ²					
t _{ON}	13		ns typ	$R_{L} = 300 \Omega, C_{L} = 35 pF,$	
ON		20	ns max	$V_S = 2 V$; Test Circuit 4	
t_{OFF}	7		ns typ	$R_L = 300 \Omega, C_L = 35 pF,$	
-011		12	ns max	$V_S = 2 \text{ V}$; Test Circuit 4	
Break-Before-Make Time Delay, t _D	7		ns typ	$R_L = 300 \Omega, C_L = 35 pF,$	
(ADG783 Only)		1	ns min	$V_{S1} = V_{S2} = 2 \text{ V}$; Test Circuit 5	
Charge Injection	3		pC typ	$V_S = 1.5 \text{ V}; R_S = 0 \Omega, C_L = 1 \text{ nF};$	
				Test Circuit 6	
Off Isolation	-58		dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 10 MHz$	
	-78		dB typ	$R_L = 50 \Omega, C_L = 5 pF, f = 1 MHz;$	
				Test Circuit 7	
Channel-to-Channel Crosstalk	-90		dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 10 MHz$; Test Circuit 8	
Bandwidth -3 dB	200		MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; Test Circuit 9	
C_{S} (OFF)	10		pF typ	f = 1 MHz	
C_D (OFF)	10		pF typ	f = 1 MHz	
$C_D, C_S(ON)$	22		pF typ	f = 1 MHz	
POWER REQUIREMENTS				$V_{\rm DD} = 3.3 \text{ V}$	
$I_{ m DD}$	0.001		μA typ	Digital Inputs = 0 V or 3.3 V	
		1.0	μA max		

REV.C -3-

 $^{^{1}}Temperature$ ranges are as follows: B Version: $-40\,^{\circ}C$ to $+85\,^{\circ}C.$

²Guaranteed by design, not subject to production test.

Specifications subject to change without notice.

ARSOLUTE MAXIMUM RATINGS1

ABSOLUTE MAXIMUM RATINGS
$(T_A = 25^{\circ}C \text{ unless otherwise noted.})$
V_{DD} to GND $$ –0.3 V to +6 V
Analog, Digital Inputs ² -0.3 V to $V_{DD} + 0.3 \text{ V}$ or
30 mA, Whichever Occurs First
Continuous Current, S or D
Peak Current, S or D 100 mA
(Pulsed at 1 ms, 10% Duty Cycle max)
Operating Temperature Range
Industrial (B Version)40°C to +85°C
Storage Temperature Range65°C to +150°C
Junction Temperature 150°C
Chip Scale Package
θ_{TA} Thermal Impedance

Lead Temperature, Soldering (10 sec)	300°C
IR Reflow (<20 sec)	235°C

NOTES

¹Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Only one absolute maximum rating may be applied at any one time.

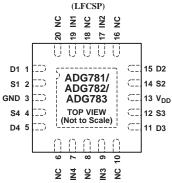
Table I. Truth Table (ADG781/ADG782)

ADG781 In	ADG782 In	Switch Condition
0	1	ON
1	0	OFF

Table II. Truth Table (ADG783)

Logic	Switch 1, 4	Switch 2, 3
0	OFF	ON
1	ON	OFF

PIN CONFIGURATION



NOTES
1. NC = NO CONNECT.
2. EXPOSED PAD TIED TO SUBSTRATE, GND.

CAUTION_

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although the ADG781/ADG782/ADG783 feature proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high-energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



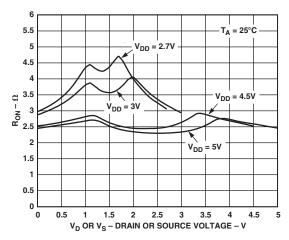
-4- REV.C

²Overvoltages at IN, S, or D will be clamped by internal diodes. Current should be limited to the maximum ratings given.

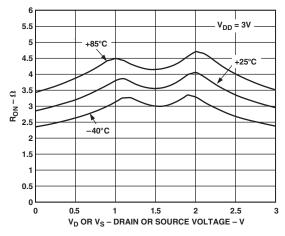
TERMINOLOGY

$V_{ m DD}$	Most positive power supply potential.	C_D , C_S (ON)	"ON" switch capacitance.
GND	Ground (0 V) reference.	t_{ON}	Delay between applying the digital control
S	Source terminal. May be an input or output.		input and the output switching on.
D	Drain terminal. May be an input or output.	$t_{ m OFF}$	Delay between applying the digital control input and the output switching off.
IN	Logic control input.	t _	"OFF" time or "ON" time measured
R_{ON}	Ohmic resistance between D and S.	t_{D}	between the 90% points of both switches,
ΔR_{ON}	On-resistance match between any two chan-		when switching from one address state to
	nels (i.e., R_{ON} max and R_{ON} min).		another (ADG783 only).
R _{FLAT(ON)}	Flatness is defined as the difference between	Crosstalk	A measure of unwanted signal that is coupled
	the maximum and minimum value of on resistance as measured over the specified		through from one channel to another as a
	analog signal range.	OCCT 1.	result of parasitic capacitance.
I _S (OFF)	Source leakage current with the switch "OFF."	Off Isolation	A measure of unwanted signal coupling through an "OFF" switch.
I _D (OFF)	Drain leakage current with the switch "OFF."	Charge	A measure of the glitch impulse transferred
$I_D, I_S (ON)$	Channel leakage current with the switch "ON."	Injection	from the digital input to the analog output
$V_{D}(V_{S})$	Analog voltage on terminals D, S.		during switching.
C _S (OFF)	"OFF" switch source capacitance.	On Response	The frequency response of the "ON" switch.
C_D (OFF)	"OFF" switch drain capacitance.	On Loss	The loss due to the on resistance of the switch.

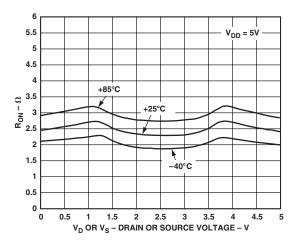
Typical Performance Characteristics



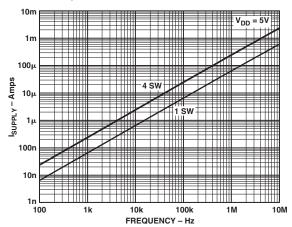
TPC 1. On Resistance as a Function of V_D (V_S)



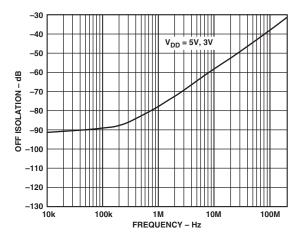
TPC 2. On Resistance as a Function of V_D (V_S) for Different Temperatures $V_{DD} = 3 \ V$



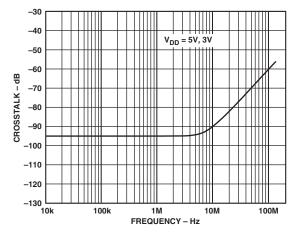
TPC 3. On Resistance as a Function of V_D (V_S) for Different Temperatures $V_{DD} = 5 \ V$



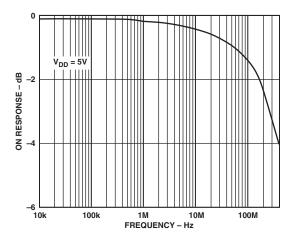
TPC 4. Supply Current vs. Input Switching Frequency



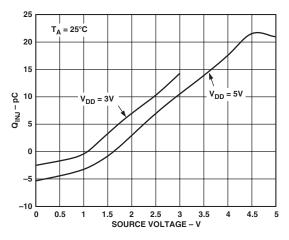
TPC 5. Off Isolation vs. Frequency



TPC 6. Crosstalk vs. Frequency



TPC 7. On Response vs. Frequency



TPC 8. Charge Injection vs. Source Voltage

APPLICATIONS

Figure 1 illustrates a photodetector circuit with programmable gain. An AD820 is used as the output operational amplifier. With the resistor values shown in the circuit, and using different combinations of the switches, gain in the range of 2 to 16 can be achieved.

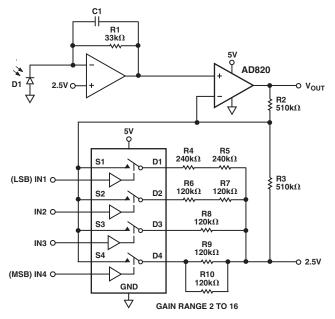
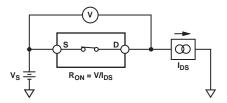
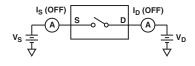


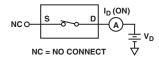
Figure 1. Photodetector Circuit with Programmable Gain

-6- REV.C

Test Circuits



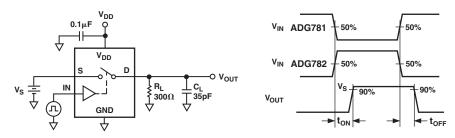




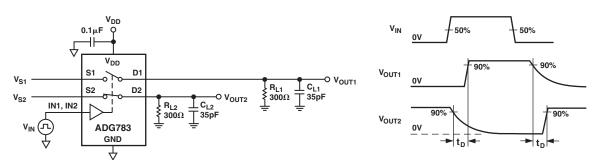
Test Circuit 1. On Resistance

Test Circuit 2. Off Leakage

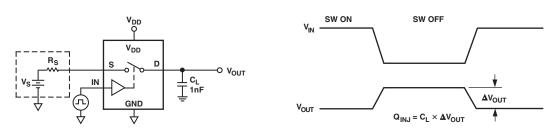
Test Circuit 3. On Leakage



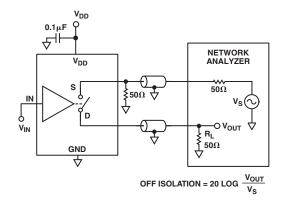
Test Circuit 4. Switching Times



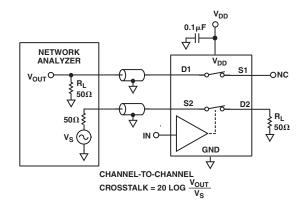
Test Circuit 5. Break-Before-Make Time Delay, t_D



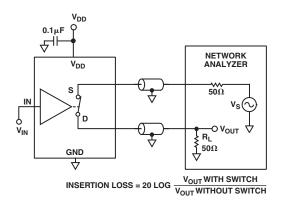
Test Circuit 6. Charge Injection



Test Circuit 7. Off Isolation



Test Circuit 8. Channel-to-Channel Crosstalk

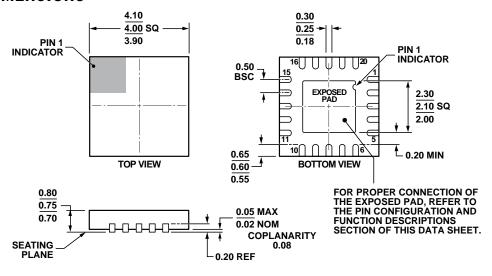


Test Circuit 9. Bandwidth

-8- REV.C

08-16-2010-B

OUTLINE DIMENSIONS



COMPLIANT TO JEDEC STANDARDS MO-220-WGGD-1.

Figure 2. 20-Lead Lead Frame Chip Scale Package [LFCSP_WQ] 4 mm × 4 mm Body, Very Very Thin Quad (CP-20-6) Dimensions shown in millimeters

ORDERING GUIDE

Model ¹	Temperature Range	Package Description	Package Option	
ADG781BCPZ	-40°C to +85°C	20-Lead Lead Frame Chip Scale Package [LFCSP_WQ]	CP-20-6	
ADG781BCPZ-REEL7	−40°C to +85°C	20-Lead Lead Frame Chip Scale Package [LFCSP_WQ]	CP-20-6	
ADG782BCPZ	-40°C to +85°C	20-Lead Lead Frame Chip Scale Package [LFCSP_WQ]	CP-20-6	
ADG782BCPZ-REEL7	−40°C to +85°C	20-Lead Lead Frame Chip Scale Package [LFCSP_WQ]	CP-20-6	
ADG783BCPZ	-40°C to +85°C	20-Lead Lead Frame Chip Scale Package [LFCSP_WQ]	CP-20-6	
ADG783BCPZ-REEL	-40°C to +85°C	20-Lead Lead Frame Chip Scale Package [LFCSP_WQ]	CP-20-6	
ADG783BCPZ-REEL7	-40°C to +85°C	20-Lead Lead Frame Chip Scale Package [LFCSP_WQ]	CP-20-6	

¹ Z = RoHS Compliant Part.

REVISION HISTORY

2/13-Rev. B to Rev. C

Changed Pin 4 from S3 to S4	1
Changes to Test Circuit 1	7
Changes to Ordering Guide)
8/12—Rev. A to Rev. B	
Updated Outline Dimensions)
Changes to Ordering Guide)
3/02—Rev. 0 to Rev. A	
Edits to Typical Performance Characteristics5-6	5
Changes to OUTLINE DIMENSIONS drawing	3

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